### **Bonn Polarized GaAs-Photoinjector**

### **ELectron Stretcher Accelerator**

anai



### Electron Stretcher Accelerator (ELSA)



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# **Generation of Polarized Electrons**



Operation, heat cleaning and activation in extreme UHV Lifetime 1000 h ↔ P (H<sub>2</sub>O, CO<sub>2</sub>) < 10<sup>-13</sup> mbar

# **Highest Polarization**



# **Typ. Photocathode Performance**



#### **Be-InGaAs/AIGaAs Superlattice**





## **Titanium-Sapphire-Laser**



max. energy: 200mJ / pulse



# **Space Charge Limited Emission**

#### **EGUN-Simulations:**





#### Measurements:





# Assembly





# The way to 10<sup>-12</sup> mbar



# **Key to Success: H-Firing!**



# Vacuum in the Storage Chamber



- Aller	0		0		CIMG 040	
	POWER		FILAMENT	AUTOMATIC ION GAUGE CONTROL		A
		EMISSION	4		MODE ANTO MODULATOR	R
1		200 MA 1 / LOD MA ZDEGAS	ON OFF		-	
		0	ÿ		Y	
	ON	States -		mbar	MANUAL CONTROL	
		DEGAS	EMISSION		9	
11	BALZERS	Sector State				

# **Electron Gun**



# **Photocathode Preparation**

- Cleaning of the PC's surface:
  - heat cleaning at ~550°C: 200°C: AsO 350°C: As (from  $As_2O_3 + 2GaAs \rightarrow Ga_2O_3 + 2As\uparrow$ ) 500°C:  $Ga_2O$
  - addition of atomic H:  $Ga_2O_3 + 4H \rightarrow Ga_2O\uparrow + 2H_2O\uparrow$

#### Activation with Cesium and Oxygen:





3,5 -

3,0 -

1,5 1,0 0,5

0,0

% 2,5 ∕ ∃0 2,0

# **Heat Cleaning**



# Hydrogen Cleaning





# **Loading Chamber**



# **Storage Chamber**



# **Storage Chamber**



# **Source of Polarized Electrons**



#### **Specific features:**

- inverted HV geometry
- adjustable perveance
- full load lock system
- H-cleaning
- P > 80% @ E = 48 keV
- $I = 200 \text{ mA} @ \tau = 1 \mu \text{s}$
- QE-lifetime > 1000 h

#### **Photocathode holder:**





# **Source of Polarized Electrons**





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## **Source and Transfer Line**



## **Electrostatic Deflector**



## Wire Scanner





# **Source and Transfer Line**



# **Space-Charge dominated Beam Transfer at 48 keV**



$$\frac{d^2x}{ds^2} + \left\{ k_x(s) + S(s) + T(s) \right\} \cdot x - \frac{\varepsilon_x^2}{x^3} - \frac{2\zeta}{x+y} = 0$$
$$\frac{d^2y}{ds^2} + \left\{ k_y(s) + S(s) + T(s) \right\} \cdot y - \frac{\varepsilon_y^2}{y^3} - \frac{2\zeta}{x+y} = 0$$

Transfer Efficiency > 99%

### **Bonn Polarized GaAs-Photoinjector**

#### Workhorse since 2000:

- spin polarization P > 80%
- pulsed beam current *I* = 100mA
- quantum life time  $\tau$  > 3000h
- transfer efficiency to LINAC > 99%
- uptime close to 100%



# new load-lock with H-cleaning upgraded to pulse currents I = 200mA

heat cleaning activation

chspannung.

